

L Number	Hits	Search Text	DB	Time stamp
-	48003	thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 12:46
-	198	thin adj film adj transistor adj array adj panel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 12:47
-	155	(thin adj film adj transistor adj array adj panel) and (pixel adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 12:48
-	92	(thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 12:49
-	87	((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and ((drain adj electrode) same (contact adj hole))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 12:51
-	88	((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 12:51
-	88	((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole) and passiv\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 12:52
-	78	((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole) and passiv\$6 and (ohmic adj contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 13:55
-	3	((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole) and passiv\$6 and (ohmic adj contact) and ((polysilicon with insulating) same doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 12:59
-	0	((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole) and passiv\$6 and (ohmic adj contact) and (photoresist\$4 same pattern\$4 same impurity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 13:57
-	57	((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole) and passiv\$6 and (ohmic adj contact) and (photoresist\$4 same pattern\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 15:02
-	57	((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole) and passiv\$6 and (ohmic adj contact) and (photoresist\$4 same pattern\$4) and impurity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 15:02

-	1	((((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole)) and passiv\$6) and (ohmic adj contact)) and ((polysilicon with insulating) same doped)) and (photoresist\$4 same pattern\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 13:58
-	0	((((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hol)) and passiv\$6) and (ohmic adj contact)) and ((photoresist\$4 with pattern\$4) same (polysilicon near3 mask))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 15:06
-	57	((((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole)) and passiv\$6) and (ohmic adj contact)) and (photoresist\$4 with pattern\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 15:06
-	0	((((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole)) and passiv\$6) and (ohmic adj contact)) and (photoresist\$4 with pattern\$4)) and (polysilicon near3 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 15:07
-	0	((((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole)) and passiv\$6) and (ohmic adj contact)) and (photoresist\$4 with pattern\$4)) and (polysilicon with mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 15:07
-	57	((((thin adj film adj transistor adj array adj panel) and ((pixel adj electrode) with passiv\$6)) and (drain adj electrode) and (contact adj hole)) and passiv\$6) and (ohmic adj contact)) and (photoresist\$4 with pattern\$4)) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 15:08